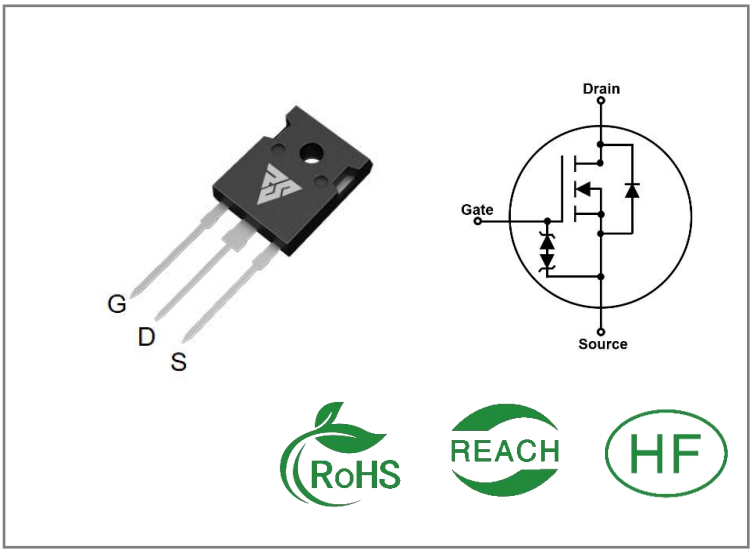
ID	R_{DS}(ON)(Max)	VDSS
25A	180mΩ	800V



Applications:

- LED Lighting
- SMPS(Switch Mode Power Supply)
- Telecom
- UPS(Uninterruptible Power Supply)

Features:

- Low gate charge
- Low RDS(on) per chip area(Low FOM)
- Extremely fast body diode
- Excellent high commutation ruggedness
- Excellent ESD robustness

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSE80R180W	T0-247	RSE80R180W	Tape	30 PCS

Absolute Maximun Ratings Tc= 2 5℃ unless otherwise specified

Symbol	Parameter	RSE80R180W	Units
VDSS	Drain-to-Source Voltage	800	V
ID	Continuous Drain Current TC=25℃	25	A
ID	Continuous Drain Current TC=100℃	16	
IDM	Pulsed Drain Current (Note*1)	75	
PD	Power Dissipation	137	W
VGS	Gate- to- Source Voltage	±20	V
EAS	Single Pulse Avalanche Engergy IAS=2.4A,VDD = 50V, RG = 25 Ω，TC=25℃	960	mJ
dv/dt	MOSFET dv/ dt ruggedness VDS = 0...400V	50	V/ns
dv/dt	Reverse diode dv/dt VDS = 0...400V, Tj = 25℃, ISD≤ID	15	V/ns
TL TPKG	Maximum Temperature for Soldering Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	300 260	℃
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RSE80R180W	Units	Test Conditions
RθJC	Junction-to-Case	0.38	℃/ W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 ℃
RθJA	Junction-to- Ambient	62.5		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	800	--	--	V	VGS=0V ID=0.25mA
IDSS	Drain- to- Source Leakage Current	--	--	1	μA	VDS=800V VGS=0V,Tj=25°C
		--	--	100	μA	VDS=800V VGS=0VTj=125°C
IGSS	Gate- to- Source Forward Leakage	--	--	1	μA	VGS=20V VDS=0V，Tj=25°C
	Gate- to- Source Reverse Leakage	--	--	-1		VGS=-20V VDS=0V,Tj=25°C

ON Characteristics TJ=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance(Note*2)	--	160	180	mΩ	VGS=10V ID=12A
VGS(TH)	Gate Threshold Voltage	3	4	5	V	VGS=VDS ID=0.25mA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	27	--	nS	VDS=400V VGS=10V ID=12A RG=4.7Ω
trise	Rise Time	--	18	--		
td(OFF)	Turn- OFF Delay Time	--	89	--		
tfall	Fall Time	--	15	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	2855	--	pF	VGS=0V VDS=500V f=1.0MHz
Coss	Output Capacitance	--	92	--		
Crss	Reverse Transfer Capacitance	--	2.4	--		
Qg	Total Gate Charge	--	58	--	nC	VDS=400V ID=12A VGS=10V
Qgs	Gate- to- Source Charge	--	16	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	20	--		
RG	Gate resistance	--	4.5	--	Ω	f = 1MHz ID = 0A(open drain)

Source- Drain Diode Characteristics

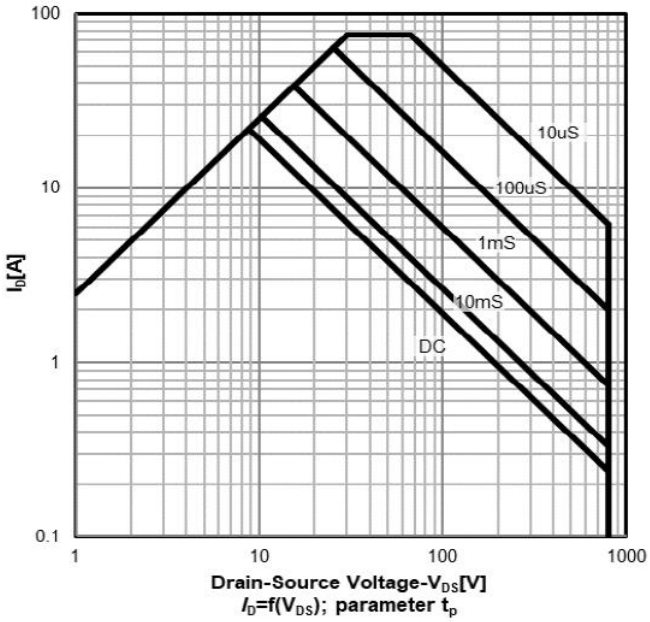
Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	25	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	100	A	
VSD	Diode Forward Voltage	--	--	1.4	V	IS=9.6A,VGS=0V
trr	Reverse Recovery Time	--	400	--	nS	VR=400V IS=12A di/dt=100A/μs
Qrr	Reverse Recovery Charge	--	6.4	--	μC	

Notes:

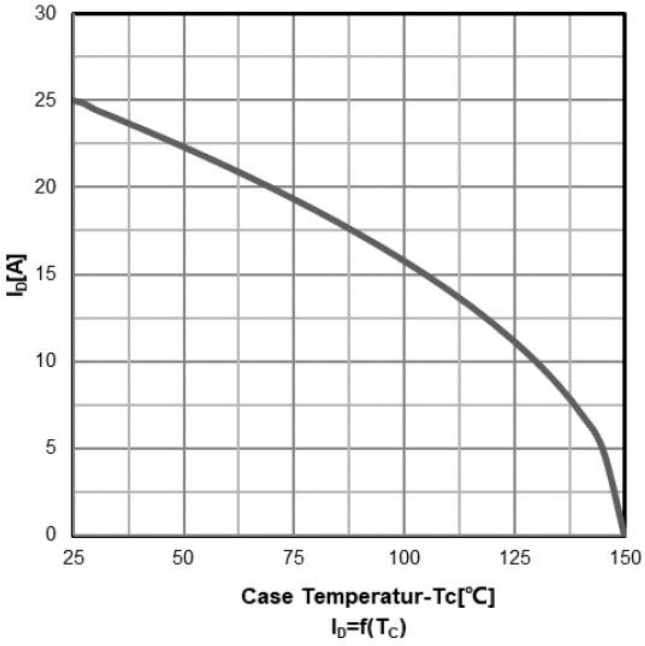
* 1. Repetitive rating; pulse width limited by maximum junction temperature.
* 2. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%

Typical Feature Curve

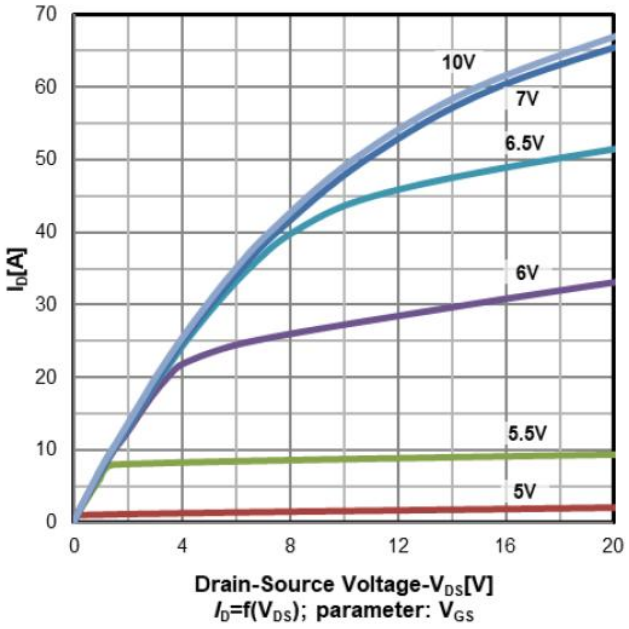
Safe operating area TC=25 ℃
Non FullPAK



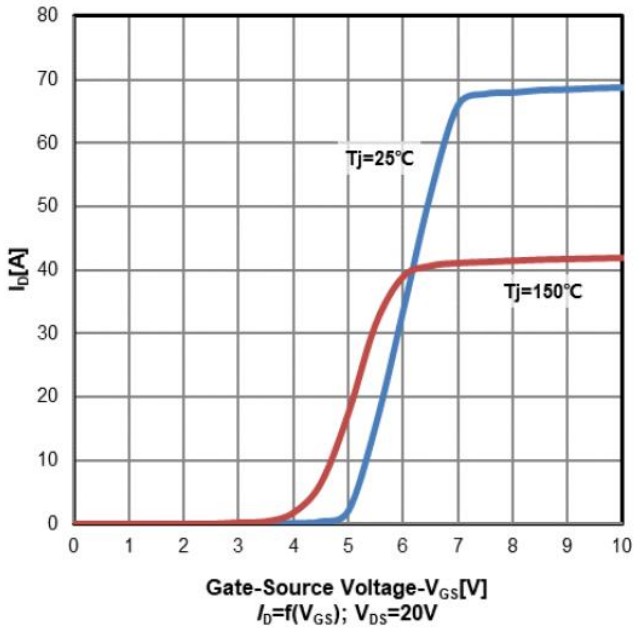
Drain current vs temperature



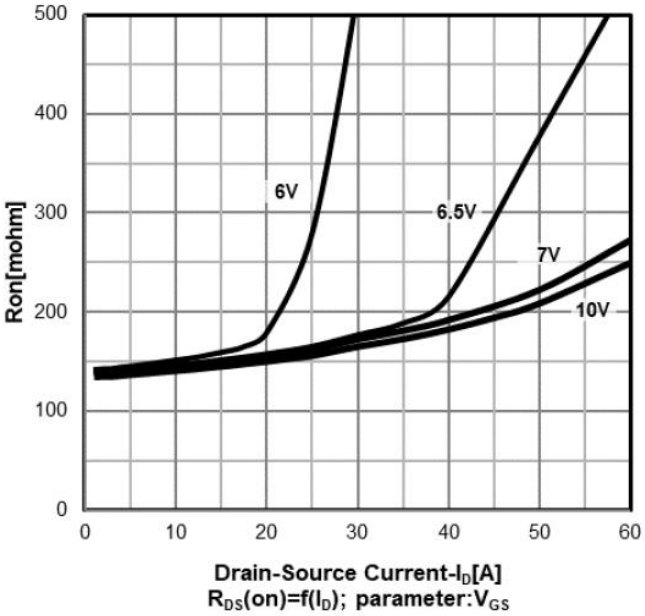
Typ. output characteristics T_j=25 ℃



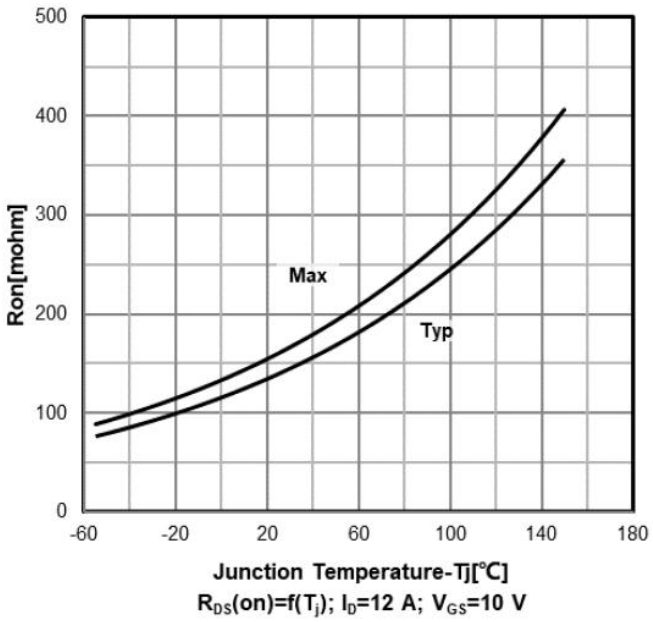
Typ. transfer characteristics



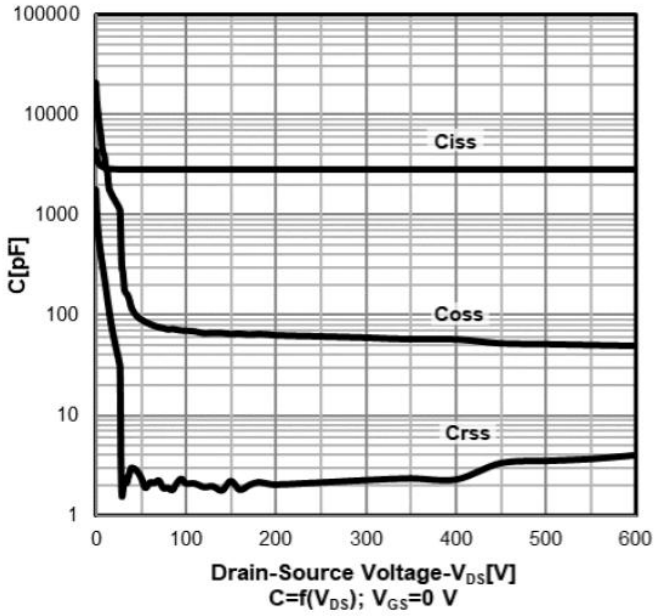
Typ. drain-source on-state resistance



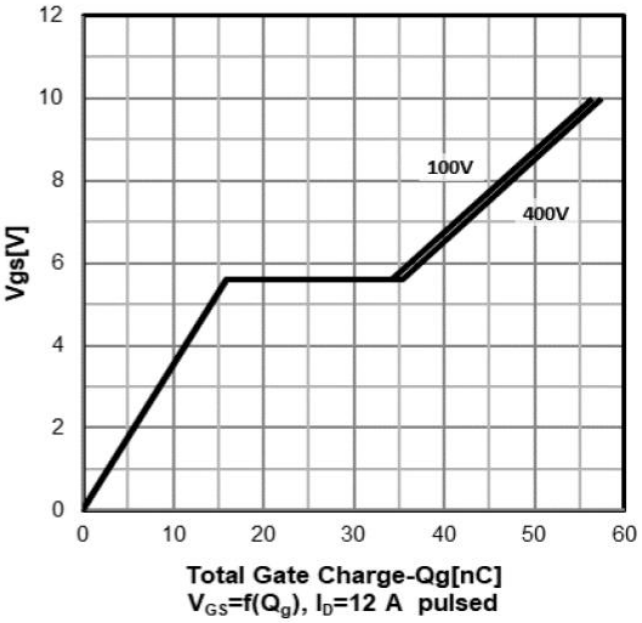
On resistance vs temperature



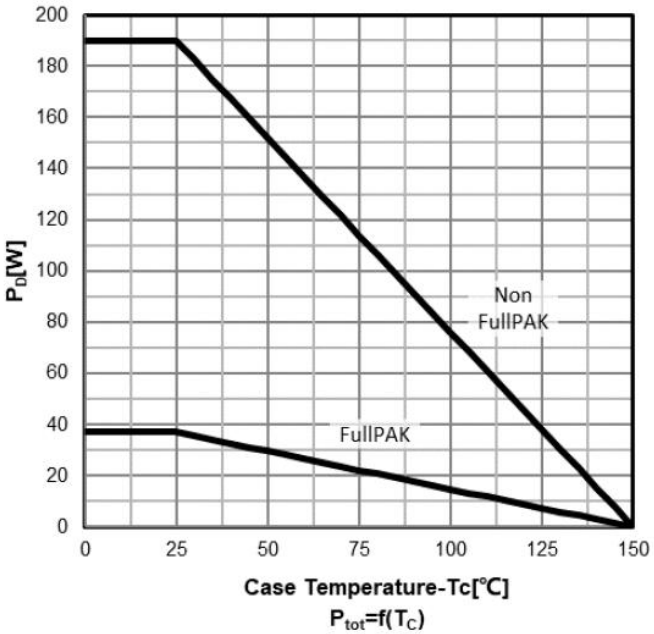
Typ. capacitances



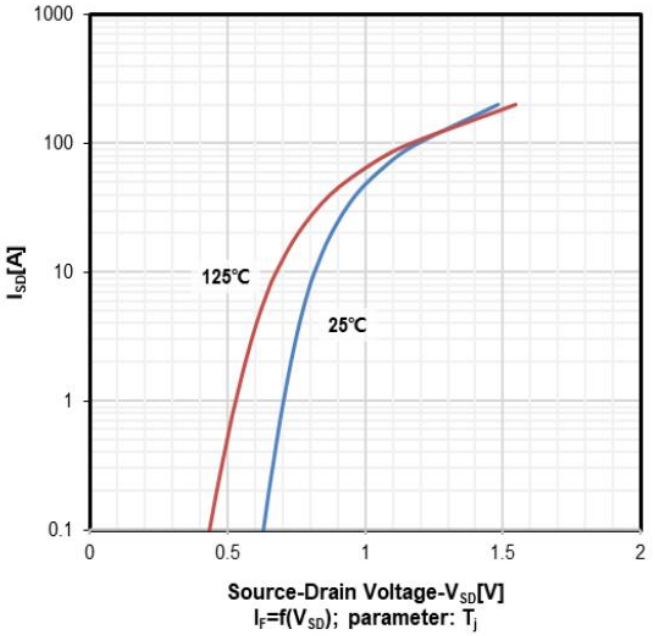
Typ. gate charge characteristics



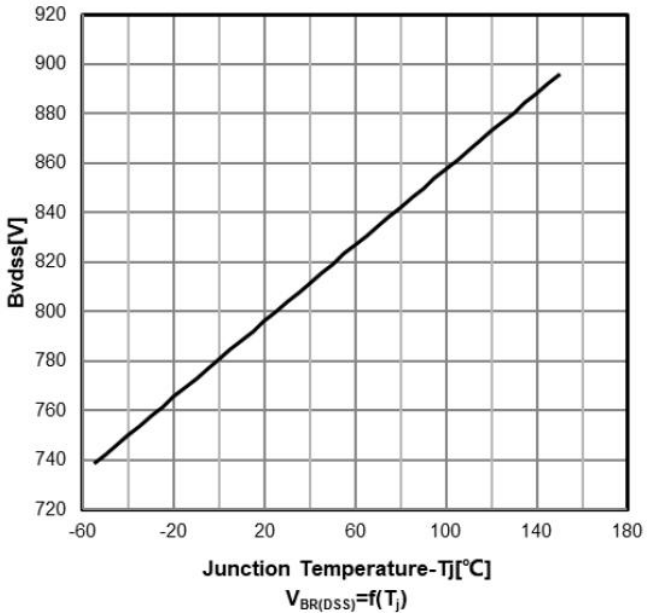
Power dissipation



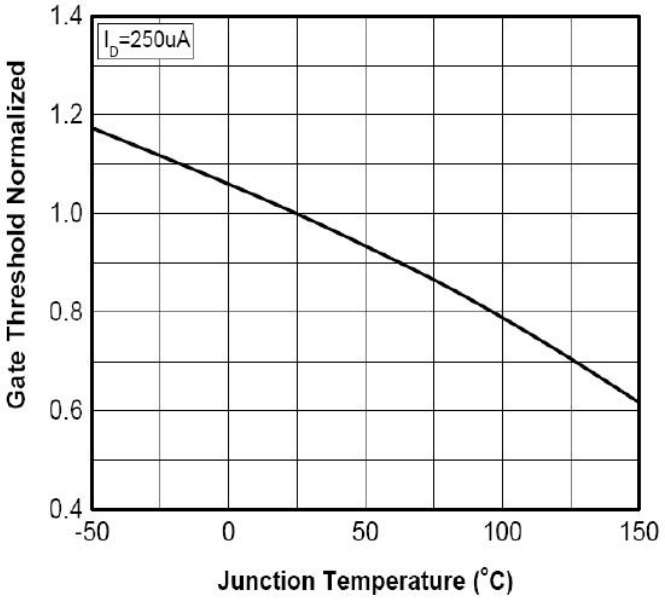
Forward characteristics of reverse diode



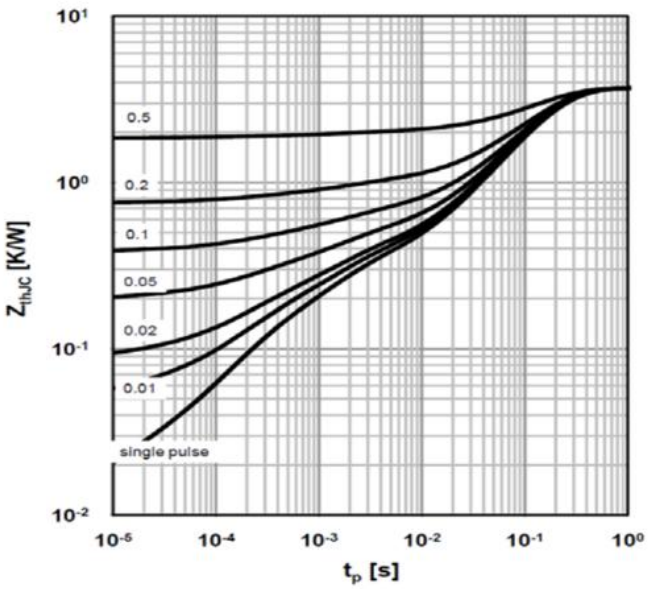
Drain-source breakdown voltage



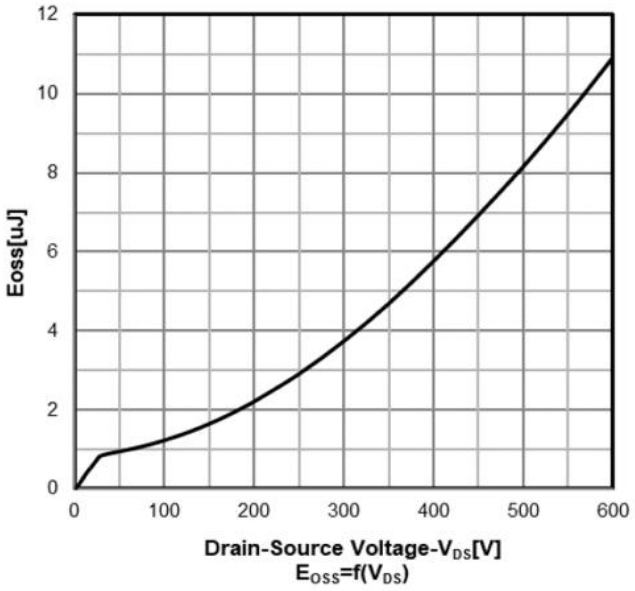
Normalized $V_{GS(th)}$ characteristics



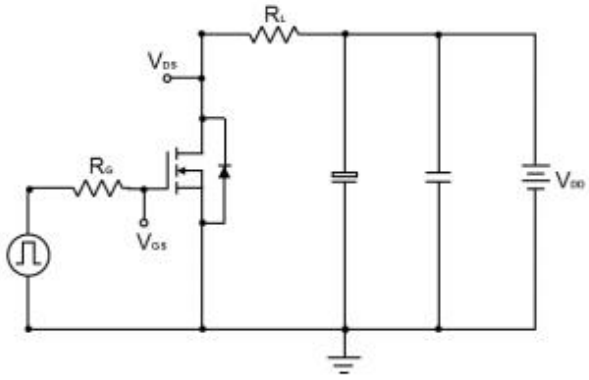
Max. transient thermal impedance parameter: D=tp/T; TO-220FullPAK



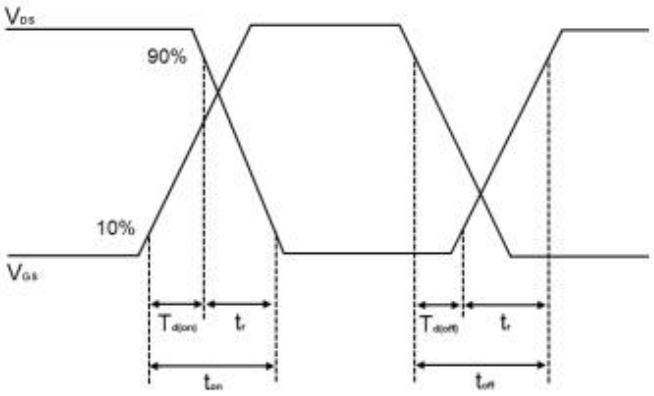
Coss stored energy



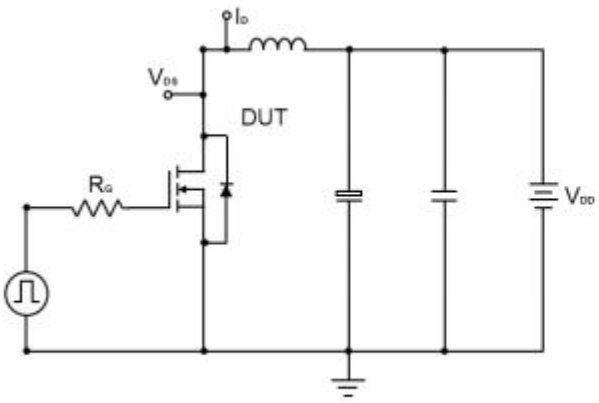
Test Circuits and Waveforms



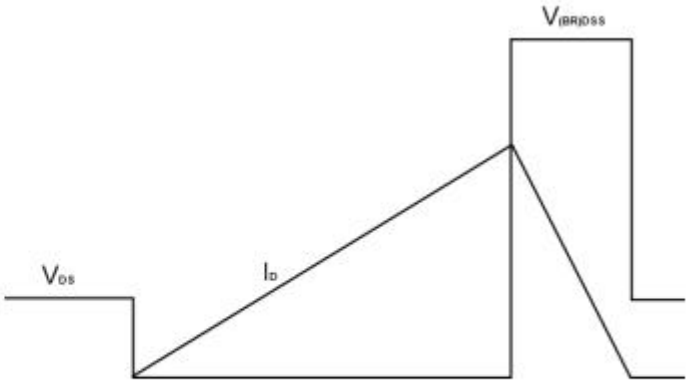
Test circuit for resistive load switching times



Switching times waveform

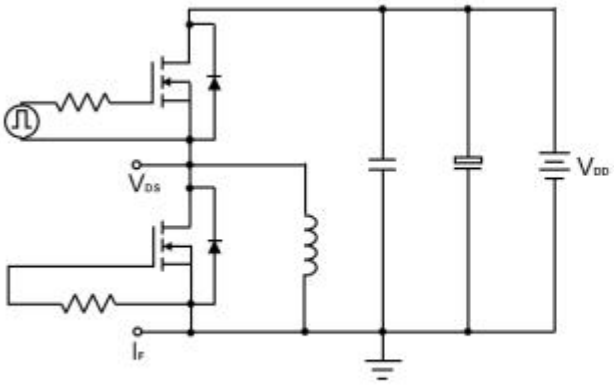


Test circuit for unclamped inductive load

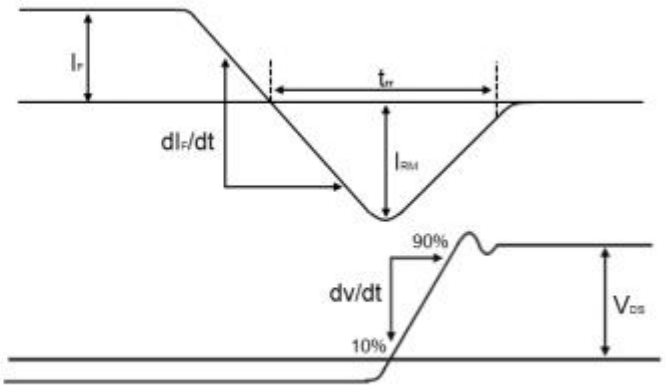


Unclamped inductive waveform

Test Circuits and Waveforms



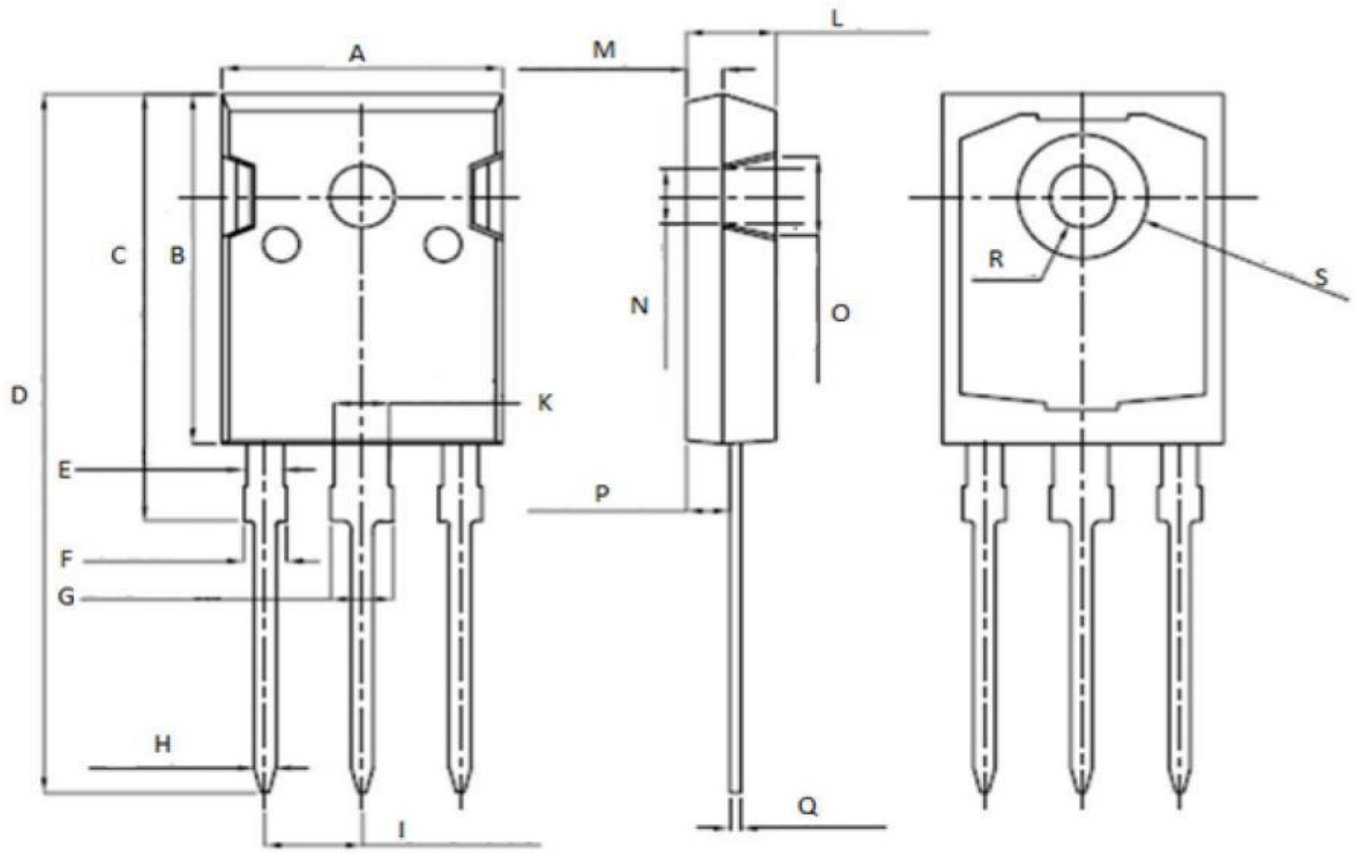
Test circuit for diode characteristics



Diode recovery waveform

Package outline drawing(TO-247 Unit: mm)

TO-247



Unit: mm		
Symbol	Min.	Max.
A	15.95	16.25
B	20.85	21.25
C	20.95	21.35
D	40.5	40.9
E	1.9	2.1
F	2.1	2.25
G	3.1	3.25
H	1.1	1.3
I	5.40	5.50

Unit: mm		
Symbol	Min.	Max.
K	2.90	3.10
L	4.90	5.30
M	1.90	2.10
N	4.50	4.70
O	5.40	5.60
P	2.29	2.49
Q	0.51	0.71
R	ϕ3.5	ϕ3.7
S	ϕ7.1	ϕ7.3

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